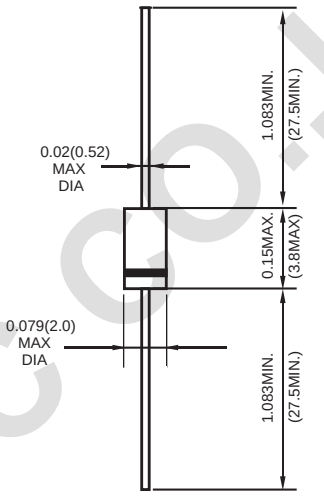
WEJ®

RoHS

1N6263

DO-35



Dimensions in inches and (millimeters)

FEATURES

- For general purpose applications
- Metal-on-silicon junction Schottky barrier which is protected by a PN junction guard ring.The low forward voltage drop and fast switching make it ideal for protection of MOS devices,steering,biasing and coupling diodes for fast switching and low logic level applications
- These diodes are also available in the Mini-MELF case with type designation LL6263,in the Micro-MELF case with type designation MCL6263

MECHANICAL DATA

- **Case:**DO-35 Glass CASE
- **Polarity:**Color band denotes cathode end
- **Weight:**Approx.0.13gram

ABSOLUTE RATINGS(LIMITING VALUES)

	SYMBOLS	VALUE	UNITS
Peak Reverse Voltage	V_{RRM}	60	V
Power Dissipation (infinite Heat Sink)	P_{tot}	400	mV
Maximum Single cycle surge 10μs square ware	I_{FSM}	2.0	A
Junction Temperature	T_J	125	℃
Storage Temperature Range	T_{STG}	-55 to +150	℃

1) Valid provided that leads at a distance of 4mm from case are kept at ambient temperature

ELECTRICAL CHARACTERISTICS

(Ratings at 25℃ ambient temperature unless otherwise specified)

	SYMBOLS	Min.	TYP.	MAX.	UNITS
Reverse Breakover Voltage at I_R=10μA	V_R	60			V
Leakage Current at V_R=50V	I_R			200	nA
Forward voltage drop at I_F=1mA I_F=15mA	V_F			0.41 1.0	V
Junction Capacitance at V_R=0V,f=1MHz	C_J			2.0	pF
Reverse Recovery time at I_F=I_R=5mA, recover to 0.1 I_R	T_{rr}			1	ns
Thermal resistance	$R_{\theta JA}$			0.3	K/W

Fig.1 Typical variation of forward. Current vs forward.voltage for primary conduction through the Schottky barrier

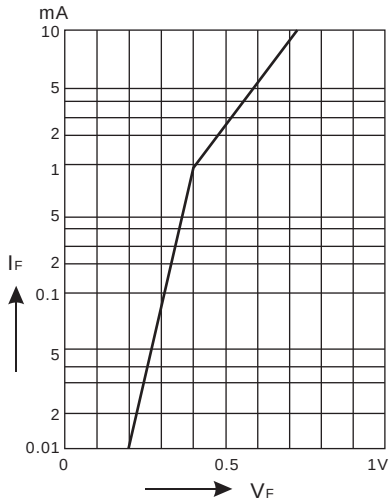


Fig.2 Typical forward conduction curve of combination Schottky barrier and PN iunction guard ring

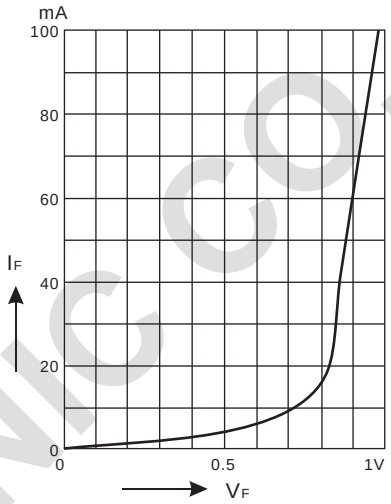


Fig.3 Typical variation of reverse current at various temperatures

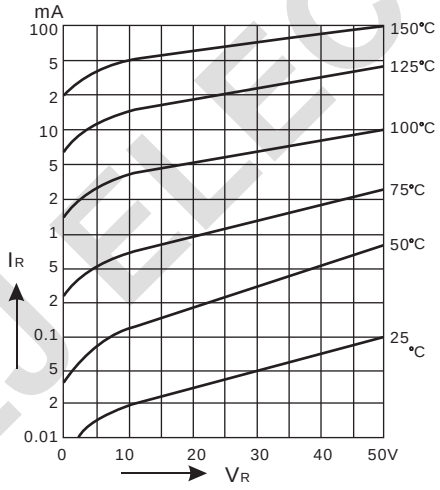


Fig.4 Typical variation curve as a function of reverse voltage